

IPXOGF22 Datasheet

Low-Power XTAL Oscillator IP in GLOBALFOUNDRIES 22FDX

1. Features

- Low Power Consumption
- Low Phase Noise
- On-Chip Tuning Capacitor Bank
- Wide operating voltage range: 1V to 1.98V
- Single-Supply Voltage Operation
- Wide Operating Temperature: -40°C to 125°C
- ESD Protection

2. Applications

- Frequency Synthesizers
- Wireless and Wired communications
- Portable and Battery-Operated Devices
- Microcontroller Clock
- Power Management

3. General Description

The IPXOGF22 is a silicon-proven ultra-low power Crystal Oscillator (XO) with amplitude detector. The amplitude detector together with synchronizers at

output buffer guarantee a glitch-free square-wave at the output. The circuit structure of this IP offers low current consumption and low complexity. The oscillator core is optimized to provide the largest oscillation amplitude and the lowest phase noise with based on the provided bias current. The IP has several programmability options and supports a wide range of crystals with different ESR values.

The IP is compatible with all *_2Mx_4Cx_1lx_* metal stack options. This means metal stacks #14, #16, and #17 readily compatible. For metal stacks #3, #8, #11, #19, #21, and #22 minor layout modification should be done by the supplier. For other metal stacks, please contact the supplier.

Contact Information

Email: info@qualinx.nl
 Website: www.qualinx.nl
 Tel: +31 15 203 2000
 Address: 2628XJ, Delftechpark 11,
 Delft, The Netherlands

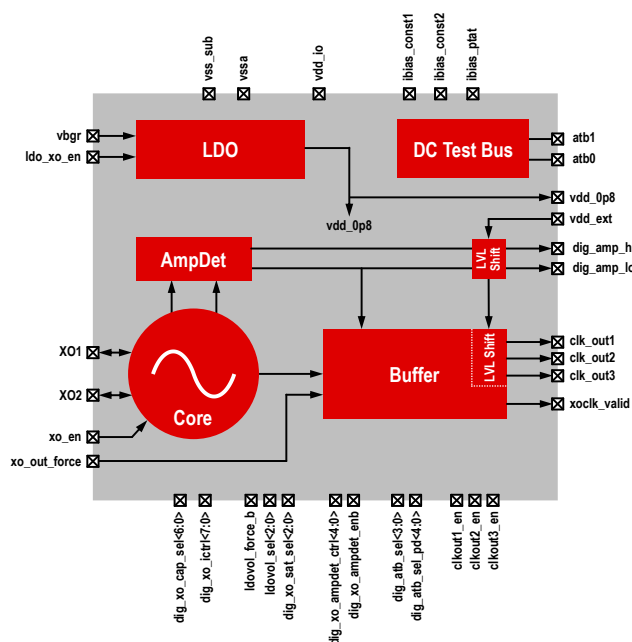


Figure 1. Functional Block Diagram

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5. Revision History

Revision 1.51: Jan 2021

- Adding detailed specifications

Revision 1.00: initial version (Nov 2020)

- Initial version
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6. Pin Configuration and Functions

Table 1. Pin Configuration and Functions

Pin Name	Metal Layer	Type	Power Domain	Description
Signal Plane				
XO1	IA	Analog In/Out	V _{DD_CORE}	XTAL connection pin #1; input clock for external mode
XO2	IA	Analog In/Out	V _{DD_CORE}	XTAL connection pin #2
clk_out1	M2	Digital Output	V _{DD_EXT}	Digital output clock signal #1
clk_out2	M2	Digital Output	V _{DD_EXT}	Digital output clock signal #2
clk_out3	M2	Digital Output	V _{DD_EXT}	Digital output clock signal #3
xoclk_valid	M2	Digital Output	V _{DD_IO}	Valid flag of output clock
atb0	C3	Analog Output	V _{DD_IO}	DC analog test bus 0, for monitoring vbgr_0p8 and v_ptat
atb1	M2	Analog Output	V _{DD_IO}	DC analog test bus 1, for monitoring LDO signals
Control Plane				
ldo_xo_en	M2	Digital Input	V _{DD_IO}	LDO enable control
ldovol_sel<2:0>	M2	Digital Input	V _{DD_IO}	Internal LDO overdrive voltage select control, from 800mV (default) to 960mV
ldovol_force_b	M2	Digital Input	V _{DD_IO}	Force LDO overdrive voltage to default (active low)
dig_xo_sat_sel<2:0>	M2	Digital Input	V _{DD_IO}	LDO number of satellites select control (thermometer code)
xo_en	M2	Digital Input	V _{DD_IO}	XO core enable
dig_xo_cap_sel<6:0>	M2	Digital Input	V _{DD_IO}	XO core capacitor control
dig_xo_ictrl<7:0>	M2	Digital Input	V _{DD_EXT}	XO core current control
clkout1_en	C2	Digital Input	V _{DD_EXT}	Enable output clock #1
clkout2_en	C2	Digital Input	V _{DD_EXT}	Enable output clock #2
clkout3_en	C2	Digital Input	V _{DD_EXT}	Enable output clock #3
dig_xo_ampdet_ctrl<4:0>	M2	Digital Input	V _{DD_EXT}	AmpDet window control (from 0 to 17)
dig_xo_ampdet_enb	C2	Digital Input	V _{DD_EXT}	AmpDet enable (active low)
dig_amp_hi	C3	Digital Output	V _{DD_EXT}	AmpDet window-high comparator output
dig_amp_lo	C3	Digital Output	V _{DD_EXT}	AmpDet window-low comparator output
dig_atb_sel_pd<4:0>	M2	Digital Input	V _{DD_IO}	atb0 multiplexer select pins. Only one of the pins should be high (one-hot code)
dig_atb_sel<3:0>	M2	Digital Input	V _{DD_IO}	atb1 multiplexer select pins. Only one of the pins should be high (one-hot code)
Power Plane				
vdd_io	IA	Analog Power	V _{DD_IO}	Main supply pin. Recommended to be directly connected to analog supply pad of the chip at top-level (star-connect)
vdd_ext	IA	Digital Power	V _{DD_EXT}	External supply voltage 0.8V
vssa	IA	Analog Ground	GND	Main ground pin. Recommended to be directly connected to analog ground pad of the chip at top-level (star-connect)
vss_sub	IA	Substrate Ground	GND	Substrate ground pin. Recommended to be directly connected to analog ground pad of the chip at top-level (star-connect)
vbgr	C4	Analog Input	V _{DD_IO}	Input reference voltage 0.8V

Pin Name	Metal Layer	Type	Power Domain	Description
ibias_const1	C3	Analog Input	V _{DD_IO}	LDO reference bias sink current 0.5 μ A
ibias_const2	M2	Analog Input	V _{DD_CORE}	Oscillator Core reference bias sink current 1 μ A
ibias_ptat	C3	Analog Input	V _{DD_CORE}	AmpDet PTAT bias sink current 1 μ A

7. Dimensions

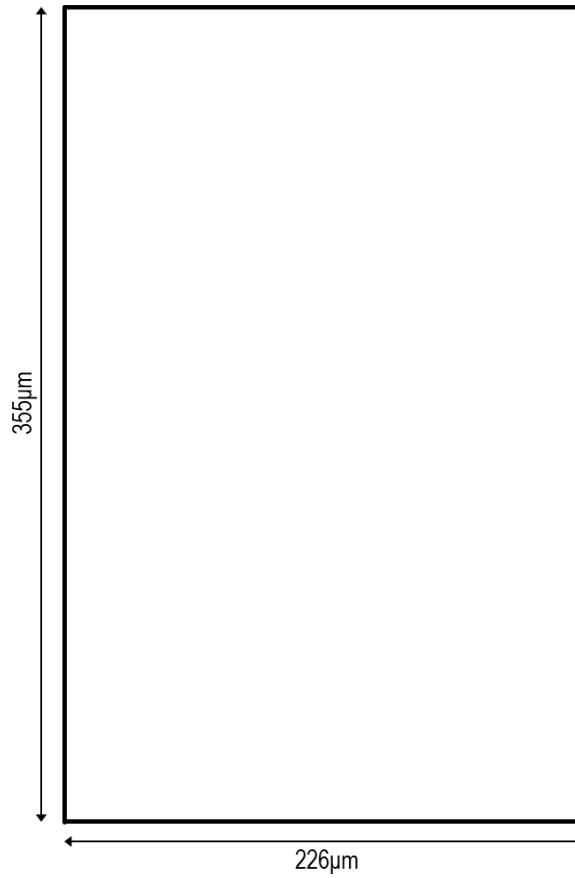


Figure 2. Dimensions Overview

8. Specifications

8.1. Electrical Characteristics

8.1.1. Operating Conditions

$T_j = 27^\circ\text{C}$, all typical voltages and currents, default settings and crystal as specified in **Error! Reference source not found.** and **Error! Reference source not found.**, unless otherwise noted.

Table 2. Operating Conditions

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Main Supply Voltage	V_{DD_IO}		1	1.8	1.98	V
External Core Supply Voltage	V_{DD_EXT}		0.72	0.8	0.88	V
Internal Core Supply Voltage	V_{DD_CORE}	Vref=0.8V	0.785	0.8	0.815	V
Input Reference Voltage	V_{REF}		0.76	0.8	0.84	V
LDO Input Reference Bias Current	I_{REF1}		0.375	0.5	0.625	μA
XO Core Input Reference Bias Current	I_{REF2}		0.75	1	1.25	μA
AmpDet Input PTAT Bias Current	I_{PTAT}	PTAT @ 27°C	0.75	1	1.25	μA
Operating Temperature	T_j		-40	27	125	$^\circ\text{C}$
LDO Boost Level	$\Delta V_{DD}/\text{code}$			40		mV/code
Supply Current	I_{DD_IO}	Default settings		175		μA
All Blocks Enabled				8.9		nA
Input High Voltage on V_{DD_IO} Domain	V_{IH_IO}		$0.7 \times V_{DD_IO}$			
Input Low Voltage on V_{DD_IO} Domain	V_{IL_IO}			$0.3 \times V_{DD_IO}$		
Input High Voltage on V_{DD_EXT} Domain	V_{IH_EXT}		$0.7 \times V_{DD_EXT}$			
Input Low Voltage on V_{DD_EXT} Domain	V_{IL_EXT}			$0.3 \times V_{DD_EXT}$		
ATB Mux On-State Resistance ¹	R_{ON}	$T_j = 27^\circ\text{C}$, atb voltage 0V to 0.95V			50	k Ω
ATB Mux Off-State Leakage to Ground ¹	I_{L_OFF}	$T_j = 27^\circ\text{C}$, atb voltage 0V to 0.95V			200	pA

¹ Each unit of ATB's analog multiplexer.

8.1.2. Oscillator Characteristics

$T_J = 27^\circ\text{C}$, all typical voltages and currents, default settings and crystal as specified in **Error! Reference source not found.** and **Error! Reference source not found.**, unless otherwise noted.

Table 3. Electrical Characteristics of Output Voltages

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Oscillation Frequency	f_{OSC}		10	24	52	MHz
On-Chip Tunable Capacitance	C_{TUNE}	Single-ended, 7-bits	1.8		31.3	pF
Oscillator Core Transconductance	g_m			4.16		ms
Oscillation Amplitude	V_{OSC}	Single-ended peak		400		mV
Startup Time	t_{STARTUP}			2.1		msec
Duty Cycle	DCY		47	50	53	%
Frequency Drift ¹	$\Delta f/\Delta T$	Excluding XTAL drift		0.006		ppm/ $^\circ\text{C}$
Output Rise Time	t_r	Output load cap = 17fF		173		ps
Output Fall Time	t_f	Output load cap = 17fF		125		ps
Phase Noise 24MHz	PN	ictrl=170 (default setting)				
		@ 10Hz		-72		dBc/Hz
		@ 100Hz		-103		dBc/Hz
		@ 1kHz		-124		dBc/Hz
		@ 10kHz		-132		dBc/Hz
		@ 100kHz		-136		dBc/Hz
Phase Noise 24MHz	PN	ictrl=50 (optimum setting ²)				
		@ 10Hz		-97		dBc/Hz
		@ 100Hz		-112		dBc/Hz
		@ 1kHz		-122		dBc/Hz
		@ 10kHz		-128		dBc/Hz
		@ 100kHz		-131		dBc/Hz

¹ Coefficient specified by "box method": The upper and lower current extremes measured over temperature define the top and bottom of the box. The sides are determined by the specified temperature range of the device. The drift of the unit is the slope of the diagonal.

² Optimized for long-term jitter.

8.1.3. Amplitude Detector

$T_J = 27^\circ\text{C}$, all typical voltages and currents, unless otherwise noted.

Table 4. Electrical Characteristics of Output Voltages

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Detection Window Size	V_{WIN}			22.5		mV
Detection Range	V_{DET}	Single-ended peak	42		444	mV
Amplitude Detection accuracy	ΔV_{DET}		-10		+10	mV
Supply Current	I_{AmDet}			2.5		μA

8.2. Typical Characteristics

$T_J = 27^\circ\text{C}$, all typical voltages and currents, default settings and typical crystal as specified in **Error! Reference source not found.** and **Error! Reference source not found.**, unless otherwise noted.

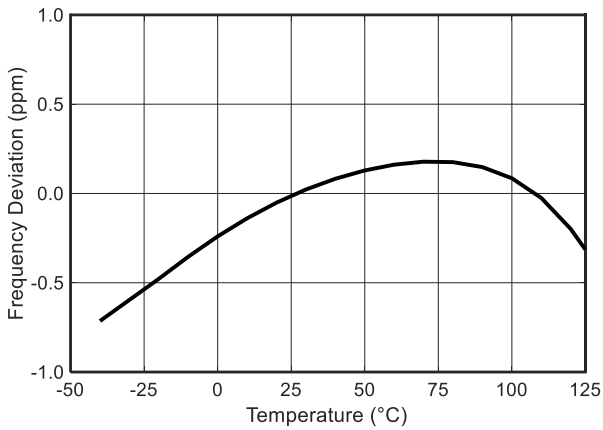


Figure 3. Frequency Error vs Temperature

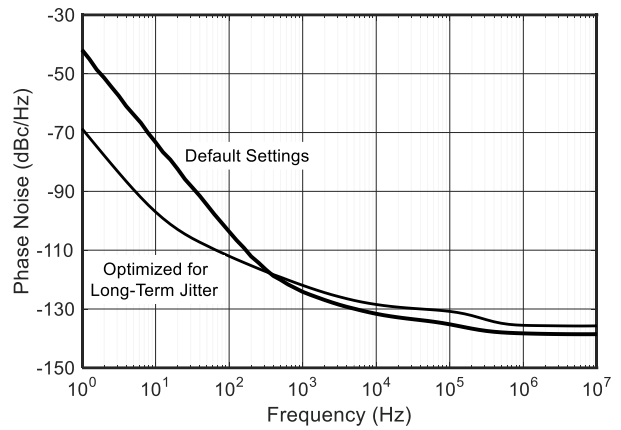


Figure 4. Output Phase Noise Spectrum

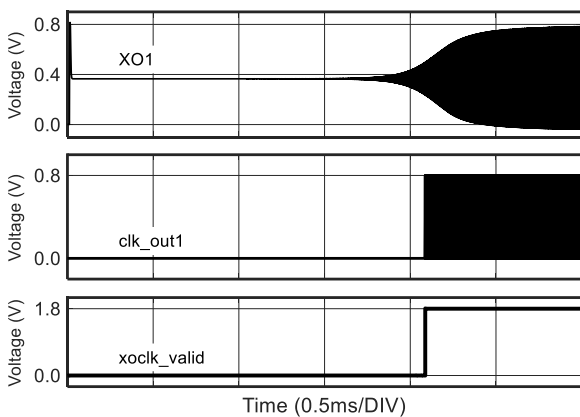


Figure 5. Startup Settling for the Default XTAL

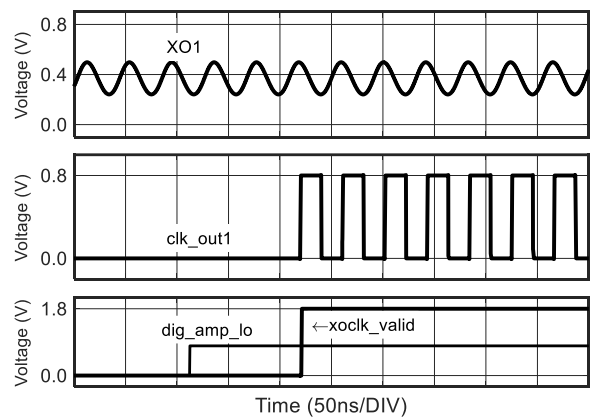


Figure 6. Startup Settling for the Default XTAL (Zoom-in).

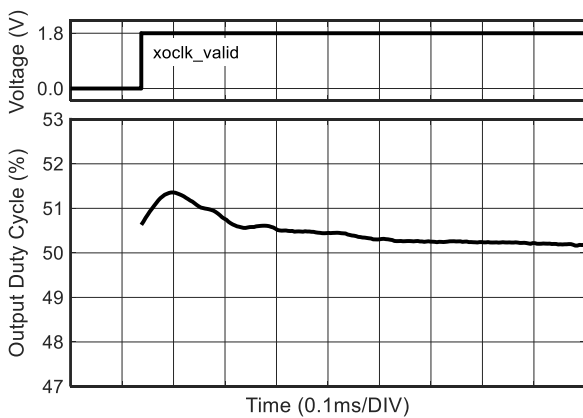


Figure 7. Output Duty Cycle vs Time for the Default XTAL

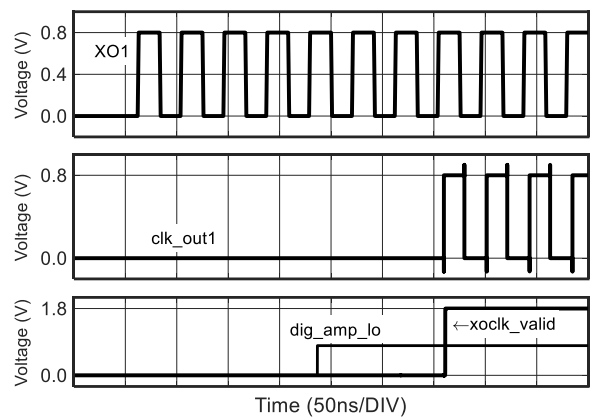


Figure 8. External Mode Startup

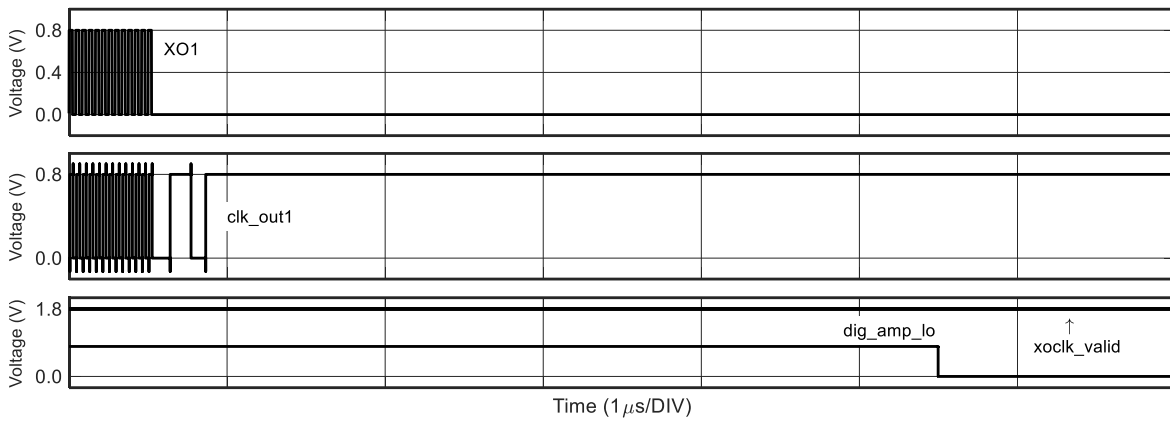


Figure 9. External Mode Stopping

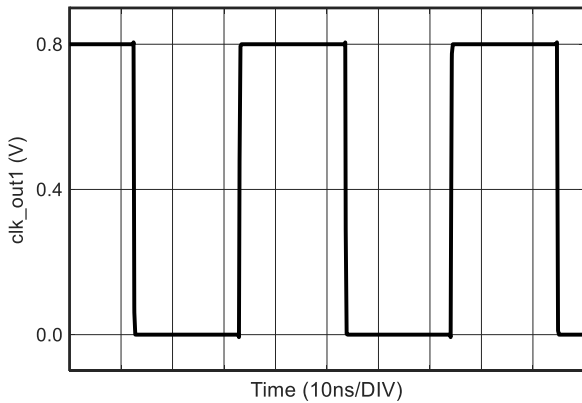


Figure 10. Typical Output Waveform

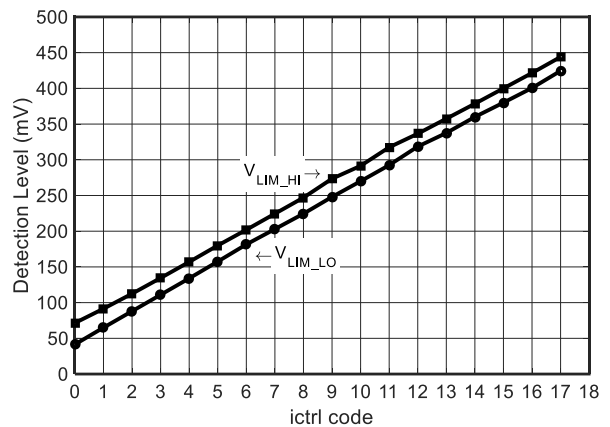


Figure 11. Amplitude Detector Characteristic

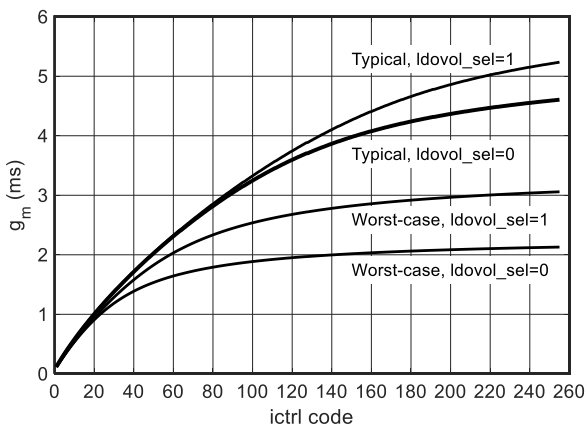


Figure 12. Oscillator Core g_m vs ictrl Code

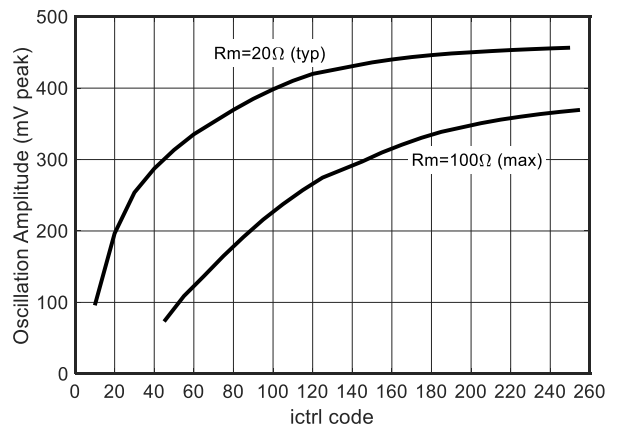


Figure 13. Oscillation Amplitude vs ictrl Code

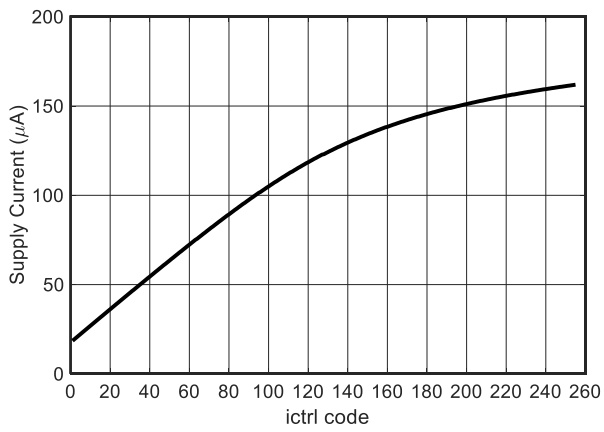


Figure 14. Current vs ictrl code

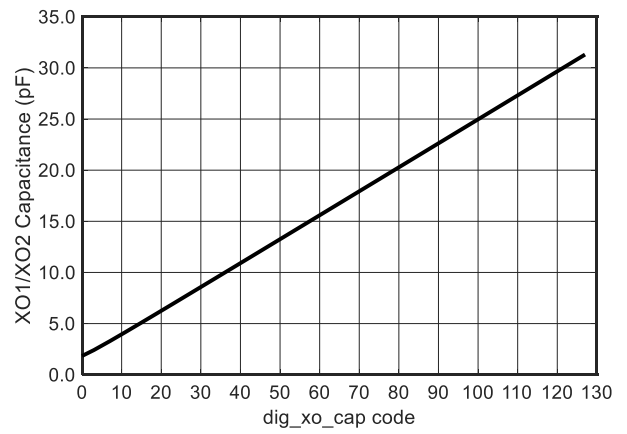


Figure 15. Load Cap vs cap_ctrl code